**Product data sheet** 

## 1. General description

Silicon Carbide Schottky diode in a TO247-2L plastic package, designed for high frequency switching mode power supplies.



### 2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T<sub>i(max)</sub> = 175 °C)
- AEC-Q101 qualified

## 3. Applications

- EV On Board Chargers
- EV DC-DC converters
- · Other EV HV systems

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol         | Parameter                       | Conditions  | Notes |            | Values |      | Unit |
|----------------|---------------------------------|---|-------|------------|--------|------|------|
| Absolute       | maximum rating                  |   |       |            |        |      |      |
| $V_{RRM}$      | repetitive peak reverse voltage |   |       |            | 1200   |      | V    |
| l <sub>F</sub> | continuous forward current      | T <sub>mb</sub> ≤ 146 °C, DC; <u>Fig. 2</u>   |       |            | 10     |      | А    |
| T <sub>j</sub> | junction temperature            |   |       | -55 to 175 |        | °C   |      |
| Symbol         | Parameter                       | Conditions  | Notes | Min        | Тур    | Max  | Unit |
| Static ch      | aracteristics                   |   |       |            |        |      |      |
| V <sub>F</sub> | forward voltage                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>  |       | -          | 1.42   | 1.60 | V    |
|                |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>   |       | -          | 1.90   | 2.30 | V    |
| Dynamic        | characteristics                 |   |       |            |        |      |      |
| $Q_r$          | recovered charge                | $I_F = 10 \text{ A; } dI_F/dt = 500 \text{ A/}\mu\text{s; } V_R = 400 \text{ V; } T_j = 25 ^{\circ}\text{C; } Fig. 7$ |       | -          | 22     | -    | nC   |

# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol   |
|-----|--------|-------------------------------------|--------------------|------------------|
| 1   | K      | cathode                             |                    | K <b>- K</b> - A |
| 2   | А      | anode                               |                    | 001aaa020        |
| mb  | mb     | mounting base; connected to cathode | TO247-2L           |                  |

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number     | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|-----------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WNSC2D101200W-A | TO247-2L     | WNSC2D101200W-A6Q     | Tube           | 30                     | TO247P-2L       | 09-Mar-2023        |

# 7. Marking

#### Table 4. Marking codes

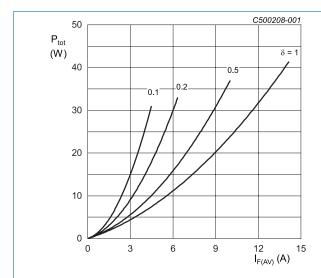
| Type number     | Marking codes       |
|-----------------|---------------------|
| WNSC2D101200W-A | WNSC2D<br>101200W-A |

# 8. Limiting values

**Table 5. Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                       | Conditions   | Notes | Values     | Unit             |
|------------------|---------------------------------|--|-------|------------|------------------|
| $V_{RRM}$        | repetitive peak reverse voltage |  |       | 1200       | V                |
| $V_{\text{RWM}}$ | crest working reverse voltage   |  |       | 1200       | V                |
| $V_R$            | reverse voltage                 | DC   |       | 1200       | V                |
| I <sub>F</sub>   | continuous forward              | T <sub>mb</sub> ≤ 146 °C, DC; <u>Fig. 2</u>                            |       | 10         | А                |
|                  | current                         | T <sub>mb</sub> ≤ 125 °C, DC; <u>Fig. 2</u>                            |       | 14         | А                |
|                  |                                 | T <sub>mb</sub> ≤ 25 °C, DC; <u>Fig. 2</u>                             |       | 27         | Α                |
| I <sub>FRM</sub> | repetitive peak forward current | $δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 125 °C$ ; square-wave pulse |       | 22         | А                |
| I <sub>FSM</sub> | non-repetitive peak             | $t_p$ = 10 ms; $T_{J(init)}$ = 25 °C; sine-wave pulse                  |       | 110        | А                |
|                  | forward current                 | $t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse                |       | 800        | А                |
| l <sup>2</sup> t | I <sup>2</sup> t for fusing     | sine-wave pulse; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 10 ms  |       | 61         | A <sup>2</sup> s |
| T <sub>stg</sub> | storage temperature             |  |       | -55 to 175 | °C               |
| T <sub>j</sub>   | junction temperature            |  |       | -55 to 175 | °C               |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$  $V_o = 1.074 \text{ V}; R_s = 0.1306 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

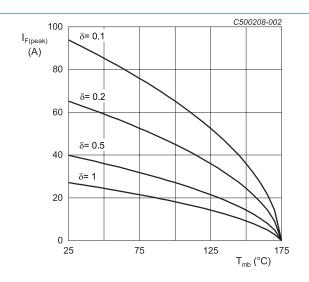
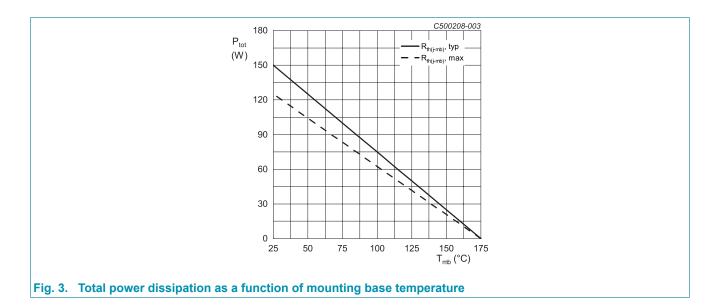


Fig. 2. Current derating as a function of mounting base temperature



### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions  | Notes | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base    | Fig. 4      |       | -   | 1   | 1.2 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient free air | in free air |       | -   | 40  | -   | K/W  |

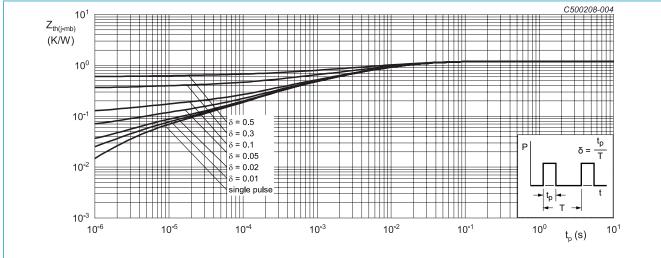
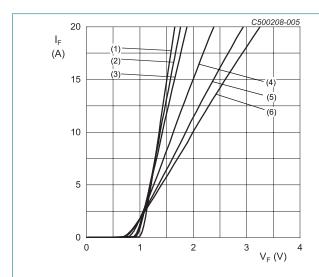


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

**Table 7. Characteristics** 

| Symbol          | Parameter                       | Conditions  | Notes | Min | Тур  | Max  | Unit |
|-----------------|---------------------------------|---|-------|-----|------|------|------|
| Static cha      | racteristics                    |   |       |     |      |      |      |
| V <sub>F</sub>  | forward voltage                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>  |       | -   | 1.42 | 1.60 | V    |
|                 |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>   |       | -   | 1.90 | 2.30 | V    |
|                 |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 175 °C; <u>Fig. 5</u>   |       | -   | 2.00 | 2.50 | V    |
| I <sub>R</sub>  | reverse current                 | V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>  |       | -   | 1    | 50   | μΑ   |
|                 |                                 | V <sub>R</sub> = 1200 V; T <sub>j</sub> = 175 °C; <u>Fig. 6</u>   |       | -   | 25   | -    | μA   |
| Dynamic         | characteristics                 |   |       |     |      |      |      |
| Q <sub>r</sub>  | recovered charge                | $I_F = 10 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 500 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 |       | -   | 22   | -    | nC   |
| C <sub>d</sub>  | diode capacitance               | f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C   |       | -   | 487  | -    | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 400 V; T <sub>j</sub> = 25 °C   |       | -   | 45   | -    | pF   |
|                 |                                 | f = 1 MHz; V <sub>R</sub> = 800 V; T <sub>j</sub> = 25 °C   |       | -   | 33   | -    | pF   |
| E <sub>as</sub> | non-repetitive avalanche energy | $I_R = 4.2 \text{ A}$ ; L = 10 mH; $T_{j(init)} = 25 ^{\circ}\text{C}$  |       | 88  | -    | -    | mJ   |



 $V_o$  = 1.074 V;  $R_s$  = 0.1306  $\Omega$ 

(1)  $T_j$  = -55 °C; typical values

(2) T<sub>j</sub> = 0 °C; typical values

(3) T<sub>i</sub> = 25 °C; typical values

(4)  $T_i = 100 \,^{\circ}\text{C}$ ; typical values

(5)  $T_j = 150$  °C; typical values

(6) T<sub>j</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

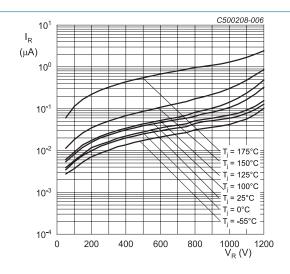
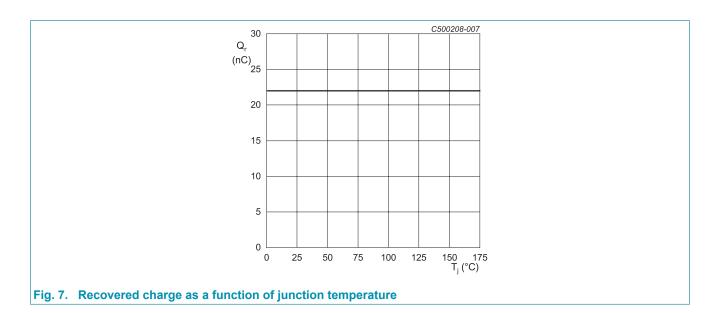
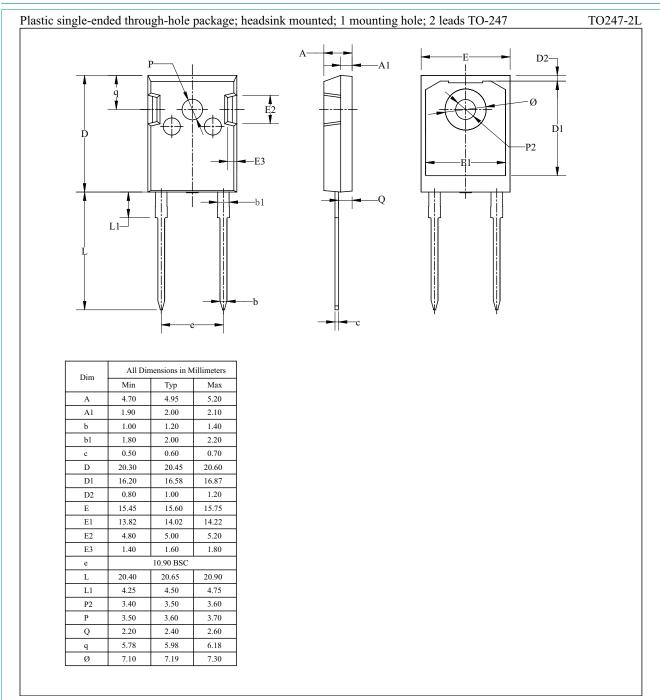


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



# 11. Package outline



## 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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